

High Voltage XPT™ IGBT

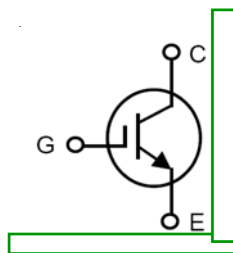
IXYF30N450

$V_{CES} = 4500V$

$I_{C110} = 17A$

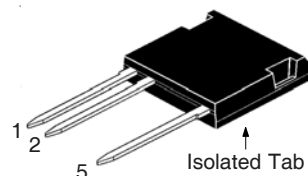
$V_{CE(sat)} \leq 3.9V$

(Electrically Isolated Tab)



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_C = 25^\circ C$ to $150^\circ C$	4500	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	4500	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	23	A
I_{C110}	$T_C = 110^\circ C$	17	A
I_{CM}	$T_C = 25^\circ C$, 1ms	190	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 15\Omega$ Clamped Inductive Load	$I_{CM} = 90$ 3600	A V
P_C	$T_C = 25^\circ C$	230	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
T_{SOLD}	Plastic Body for 10 seconds	260	$^\circ C$
F_C	Mounting Force	20..120 / 4.5..27	Nm/lb.in.
V_{ISOL}	50/60Hz, 1 Minute	4000	V~
Weight		5	g

ISOPLUS i4-Pak™


 1 = Gate
 2 = Emitter
 5 = Collector

Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 4000V~ Electrical Isolation
- High Blocking Voltage
- High Peak Current Capability
- Low Saturation Voltage

Advantages

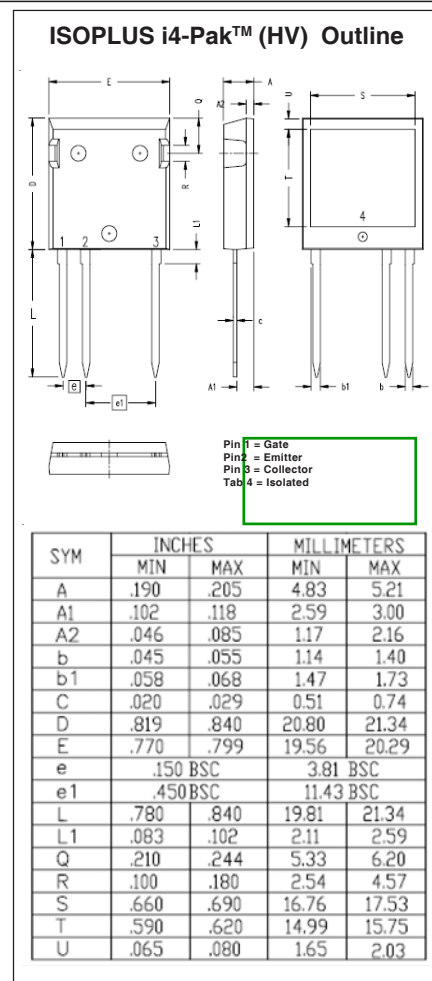
- Low Gate Drive Requirement
- High Power Density

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- Laser Generators
- Capacitor Discharge Circuits
- AC Switches

Symbol	Test Conditions ($T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	4500		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	3.0		V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ Note 2, $T_J = 100^\circ C$		100	25 μA μA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 25V$			± 200 nA
$V_{CE(sat)}$	$I_C = 30A$, $V_{GE} = 15V$, Note 1 $T_J = 125^\circ C$		3.2 4.5	V V

Symbol Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 30\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	11	18	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		1840	pF
C_{oes}			83	pF
C_{res}			35	pF
Q_g	$I_C = 30\text{A}, V_{GE} = 15\text{V}, V_{CE} = 1000\text{V}$		88	nC
Q_{ge}			11	nC
Q_{gc}			40	nC
$t_{d(on)}$	Resistive Switching Times, $T_J = 25^\circ\text{C}$ $I_C = 30\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 960\text{V}, R_G = 15\Omega$		38	ns
t_r			318	ns
$t_{d(off)}$			168	ns
t_f			1220	ns
R_{thJC}				0.54 $^\circ\text{C/W}$
R_{thCS}		0.15	$^\circ\text{C/W}$	
$t_{d(on)}$	Resistive Switching Times, $T_J = 125^\circ\text{C}$ $I_C = 30\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 960\text{V}, R_G = 15\Omega$		42	ns
t_r			590	ns
$t_{d(off)}$			180	ns
t_f			1365	ns



Notes:

1. Pulse test, $t < 300\mu\text{s}$, duty cycle, $d < 2\%$.
2. Device must be heatsunk for high-temperature leakage current measurements to avoid thermal runaway.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

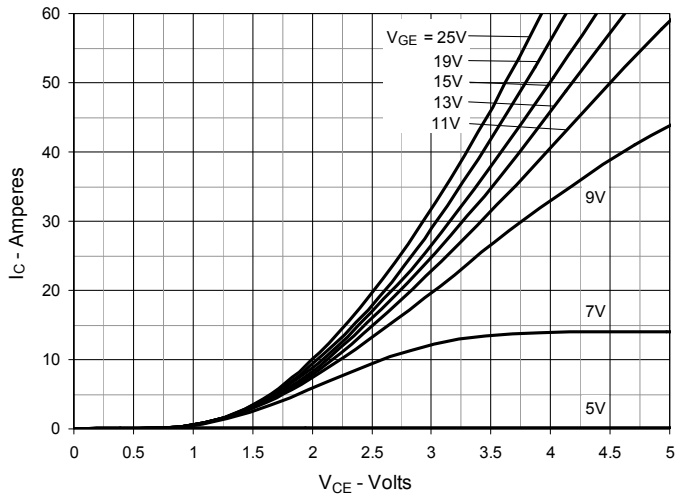
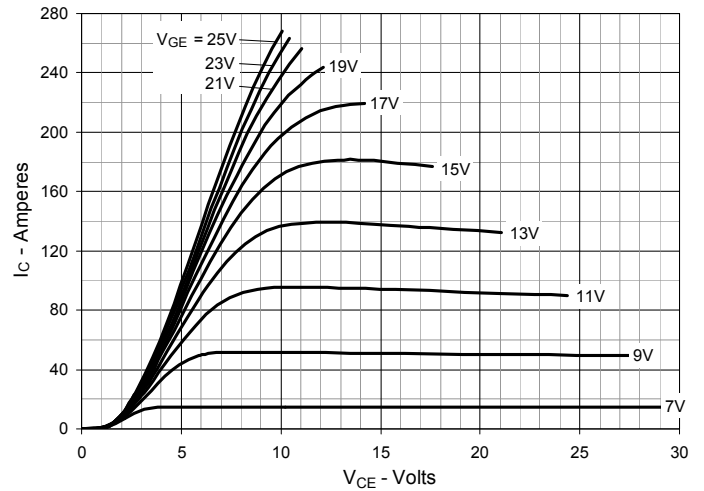
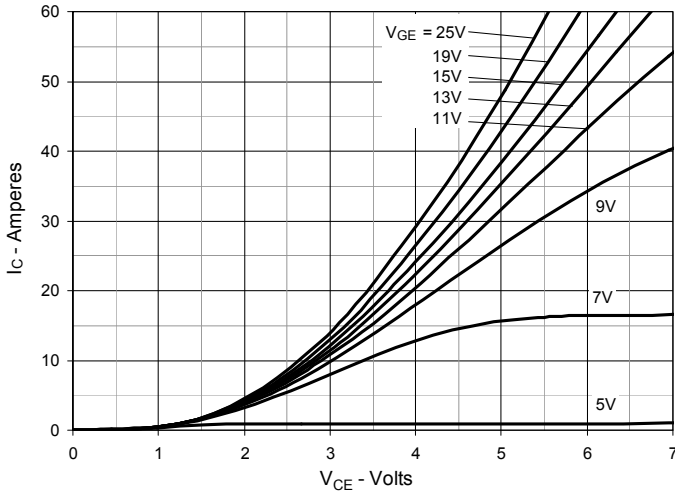
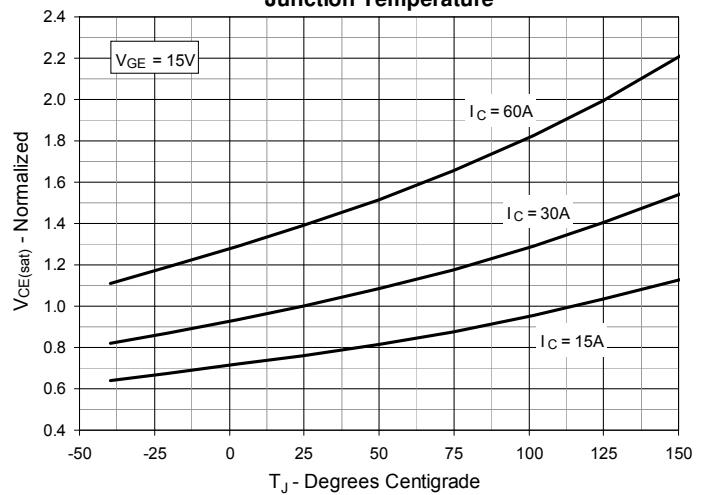
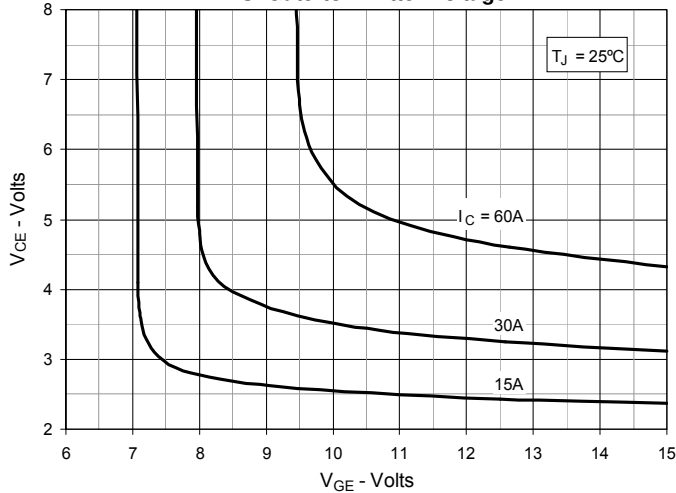
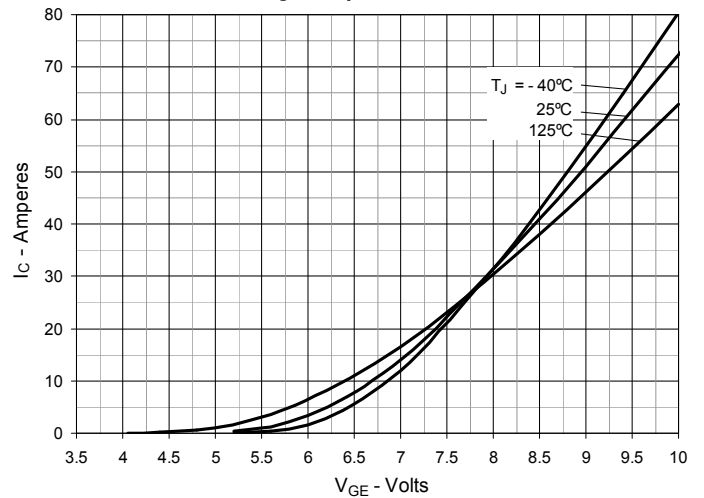
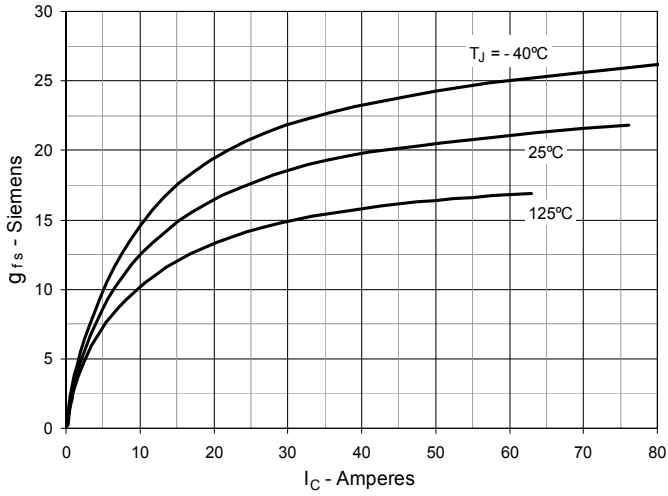
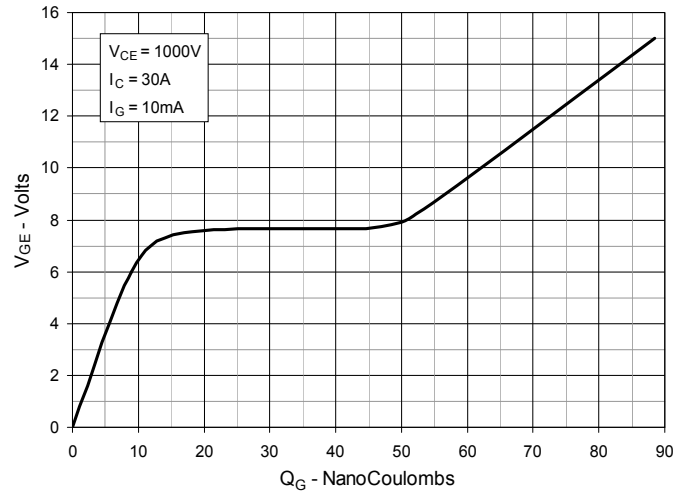
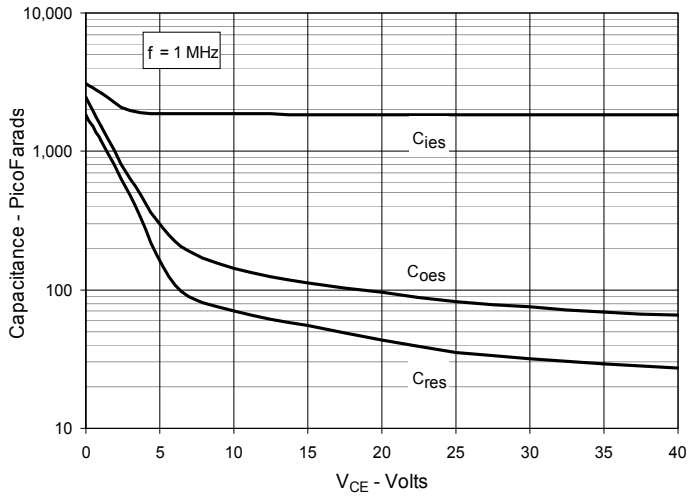
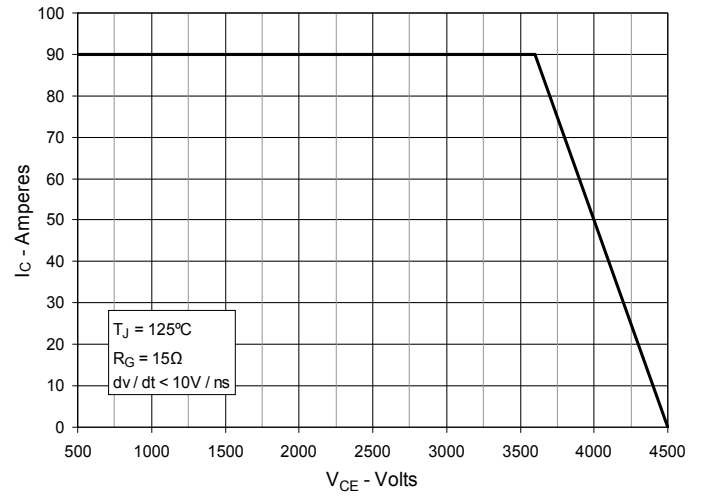
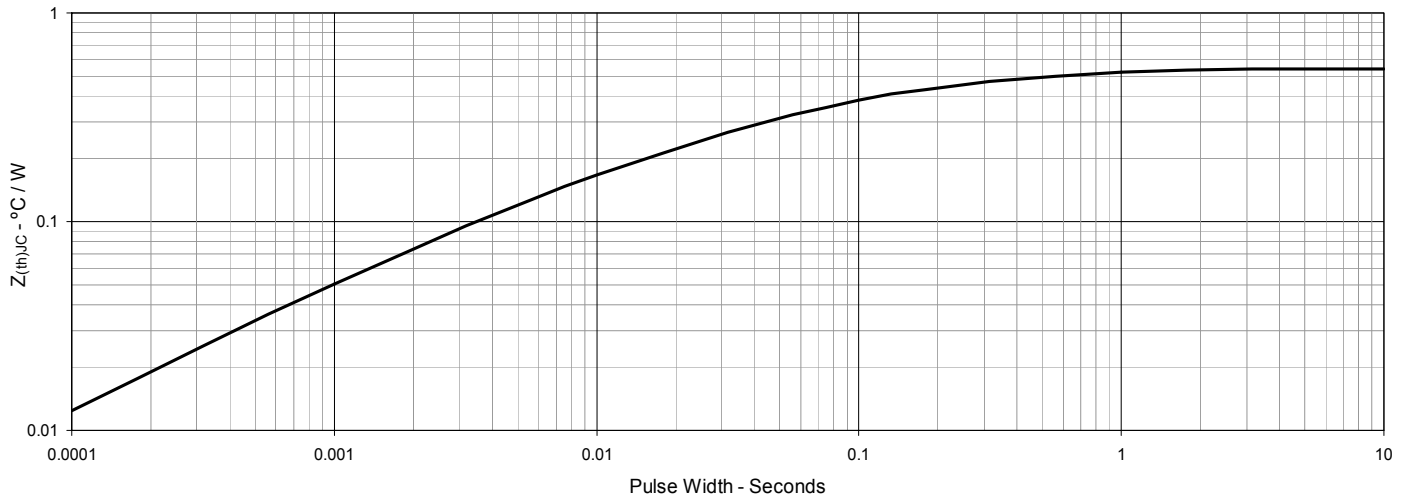
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 6. Input Admittance


Fig. 7. Transconductance

Fig. 8. Gate Charge

Fig. 9. Capacitance

Fig. 10. Reverse-Bias Safe Operating Area

Fig. 11. Maximum Transient Thermal Impedance


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